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IN THE CLAIMS

Please amend claims 29, 30, and 33 as follows:

Claims 1 -28. (Canceled)

1           29. (Currently Amended) A flat panel display, comprising a plurality of sub-pixels  
2         driven by thin film transistors, each of the thin film transistors including a source electrode,  
3         a drain electrode, a gate electrode, and a polysilicon semiconductor layer and each of the  
4         sub-pixels including a first electrode, a second electrode, and an emitting layer disposed  
5         between the first electrode and the second electrode, wherein one of the source electrode and  
6         the drain electrode includes:

7                 a first titanium layer contacting the semiconductor layer;

8                 an aluminum-based metal layer arranged on the first titanium layer;

9                 a second titanium layer arranged on the aluminum-based metal layer and  
10      contacting the first electrode;

11                 a first titanium nitride layer disposed between the first titanium layer and the  
12      aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first  
13      titanium layer and aluminum from the aluminum-based metal layer reacting with each other;  
14      and

15                 a second titanium nitride layer disposed between the second titanium layer and  
16      the aluminum-based metal layer, the second titanium nitride layer preventing titanium from

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17       the second titanium layer and aluminum from the aluminum-based metal layer reacting with  
18       each other;

19               wherein the titanium nitride layer contains layers contain 5 to 85wt% of  
20       nitrogen.

1               30. (Currently Amended)   The flat panel display of claim 29, wherein the first  
2       titanium nitride layer has a thickness of about 100 to 600Å.

1               31. (Previously Presented)   The flat panel display of claim 29, wherein the first  
2       titanium nitride layer has a thickness of about 100 to 400Å.

1               32. (Previously Presented)   The flat panel display of claim 29, wherein the second  
2       titanium nitride layer has a thickness of about 200 to 600Å.

1               33. (Currently Amended)   The flat panel display of claim 29, wherein the second  
2       titanium nitride layers have layer has a thickness of about 300Å.

1               34. (Previously Presented)   A flat panel display, comprising a plurality of  
2       sub-pixels driven by thin film transistors, each of the thin film transistors including a source  
3       electrode, a drain electrode, a gate electrode, and a polysilicon semiconductor layer each of  
4       the sub-pixels including a first electrode, a second electrode, and an emitting layer disposed

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5       between the first electrode and the second electrode, wherein one of the source electrode and  
6       the drain electrode includes:

7                 a first titanium layer contacting the semiconductor layer;  
8                 an aluminum-based metal layer arranged on the first titanium layer;  
9                 a second titanium layer arranged on the aluminum-based metal layer and  
10      contacting the first electrode;

11                 a first titanium nitride layer disposed between the first titanium layer and the  
12      aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first  
13      titanium layer and aluminum from the aluminum-based metal layer reacting with each other;  
14      and

15                 a second titanium nitride layer disposed between the second titanium layer and  
16      the aluminum-based metal layer, the second titanium nitride layer preventing titanium from  
17      the second titanium layer and aluminum from the aluminum-based metal layer reacting with  
18      each other;

19                 wherein the aluminum-based metal layer is an aluminum alloy containing about  
20      0.5 to 5 wt% of one element being selected from the group consisting of silicon, copper,  
21      neodymium, platinum, and nickel.

1       35. (Previously Presented)   The flat panel display of claim 34, wherein the  
2       aluminum-based metal layer is an aluminum-silicon alloy containing about 2 wt% of silicon.